Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT428 (DPAK) surface-mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Features and benefits

- · 3Q technology for improved noise immunity
- High blocking voltage capability
- · High commutation capability with maximum false trigger immunity
- · High immunity to false turn-on by dV/dt
- Less sensitive gate for very high noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in three quadrants only

3. Applications

- · General purpose motor control circuits
- Home appliances
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 107 \text{ °C}$; $\overline{\text{Fig. 1}}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$		-	-	4	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5		-	-	25	Α
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms		-	-	27	Α
Tj	junction temperature			-	-	125	°C
Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	50	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	30	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
Dynamic chara	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 4 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	6	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	[]	T2——T1
2	T2	main terminal 2	(7 B S)	G sym051
3	G	gate		Symost
mb	T2	mounting base; main terminal 2		
			DPAK (SOT428)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BTA204S-600B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 107 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	4	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	25	Α
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms	-	27	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	3.1	A²s
dl _T /dt	rate of rise of on-state current	I _G = 100 mA	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

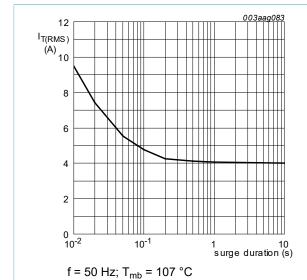


Fig. 1. RMS on-state current as a function of surge duration; maximum values

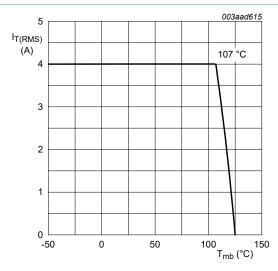


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

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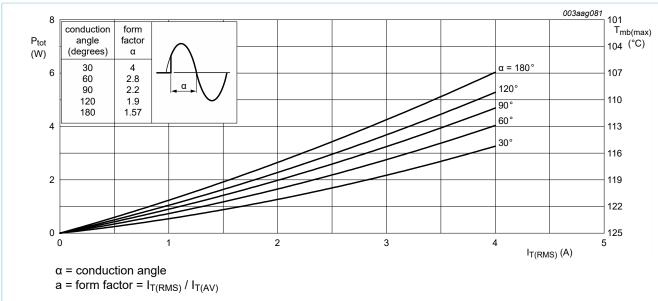


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

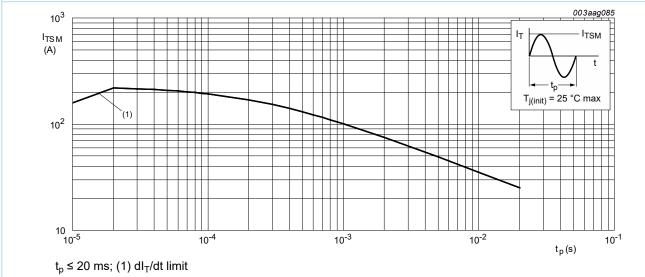


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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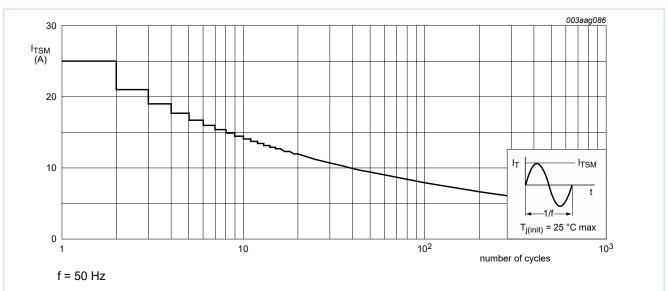
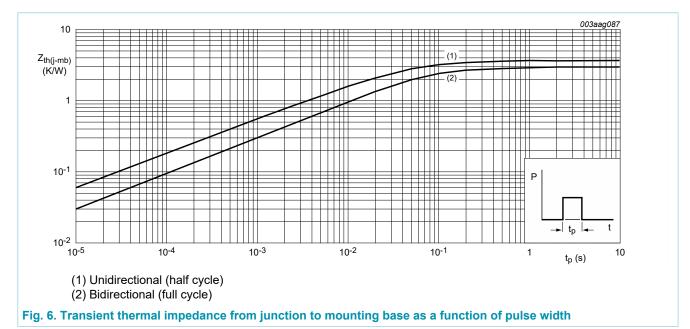


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	3	K/W
		half cycle; Fig. 6	-	-	3.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	75	-	K/W



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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	-	50	mA
lL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	-	45	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	30	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	30	mA
V _T	on-state voltage	I _T = 5 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics		,			-
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 4 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	6	-	-	A/ms

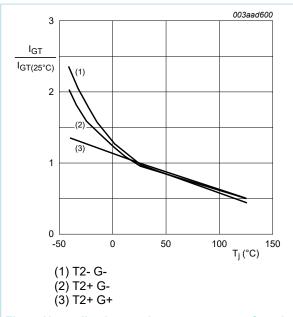


Fig. 7. Normalized gate trigger current as a function of junction temperature

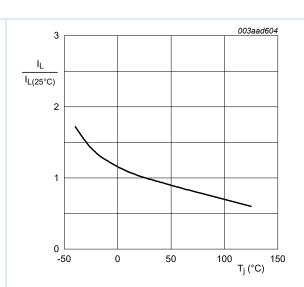


Fig. 8. Normalized latching current as a function of junction temperature

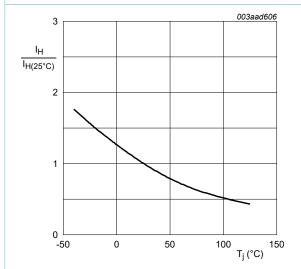
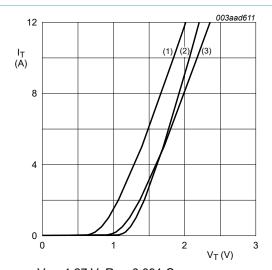


Fig. 9. Normalized holding current as a function of junction temperature

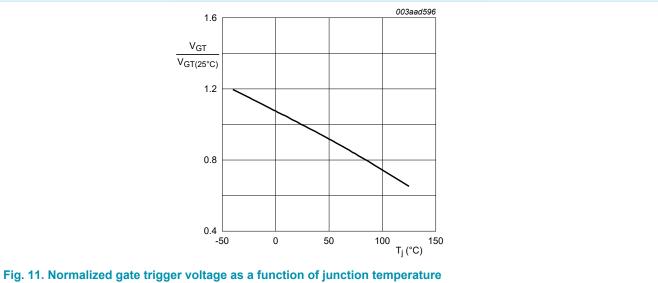


 V_o = 1.27 V; R_s = 0.091 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values (3) T_j = 25 °C; maximum values

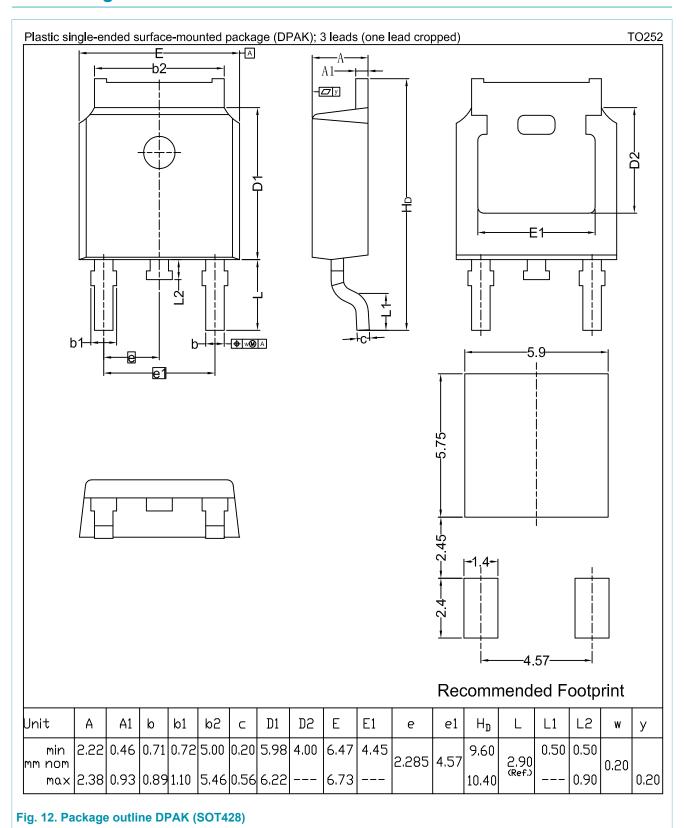
Fig. 10. On-state current as a function of on-state voltage

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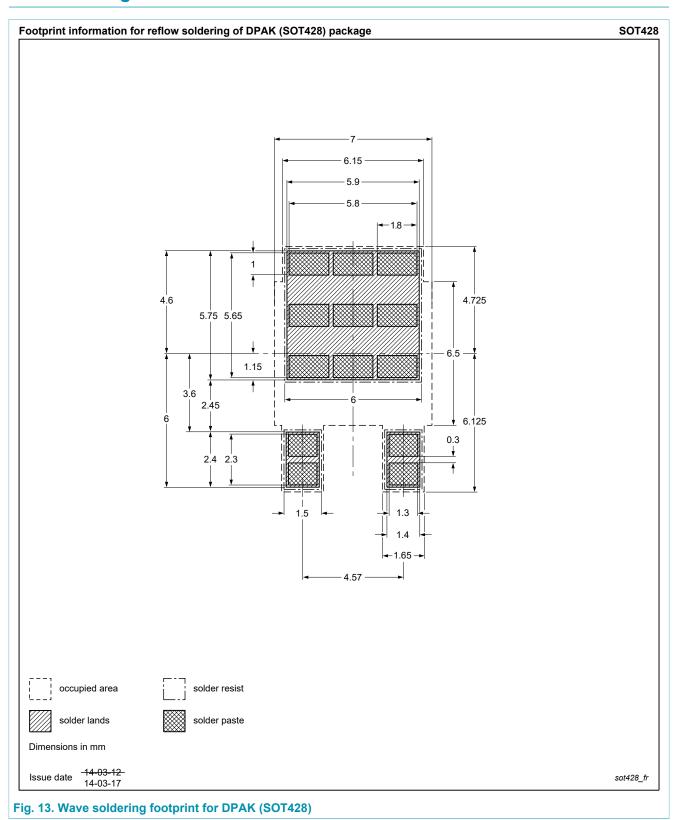


10. Package outline



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11. Soldering



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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